

## **ABSTRACT**

### **ETCH OF SILICON NITRIDE SELECTIVE TO SILICON AND SILICON DIOXIDE USEFUL DURING THE FORMATION OF A SEMICONDUCTOR DEVICE**

A method for etching silicon nitride selective to silicon dioxide and silicon (polycrystalline silicon or monocrystalline silicon) comprises the use of oxygen along with an additional etchant of either  $\text{CHF}_3$  or  $\text{CH}_2\text{F}_2$ . Flow rates, power, and pressure settings are specified.

09854206-051101